

**AMENDMENTS TO THE CLAIMS**

**This listing of claims will replace all prior versions and listings of claims in the application:**

**LISTING OF CLAIMS:**

Claims 1-5 (canceled)

Claim 6 (currently amended): A method for polishing a metal film on a semiconductor substrate, comprising the steps of:

providing a semiconductor substrate comprising a metal film and an insulating film therein;

providing a polishing composition comprising alumina fine particles containing or not containing aluminum hydrate, a polishing accelerator and water, said alumina fine particles having an  $\alpha$  conversion ratio of from 68 to 90% and a specific surface area of from 31 to 77 m<sup>2</sup>/g, and

mechanochemically polishing a metal film on said semiconductor substrate with said polishing composition,

wherein said metal of said metal film is selected from the group consisting of tungsten, aluminum, copper and alloys thereof.

Claim 7 (canceled)

Claim 8 (original): The method according to claim 6, wherein said insulating layer is made of a material selected from oxidized silicon and nitrided silicon.

Claim 9 (original): The method according to claim 6, wherein said metal film is of tungsten, said insulating layer is of oxidized silicon, and a selection ratio of polishing between said tungsten and oxidized silicon is above 200.